

Characteristics	Symbol	FTGBU406	FTGBU1006	FTGBU1206	FTGBU1606	FTGBU2006	FTGBU3006	UNIT
Maximum Recurrent Reverse Voltage	VRRM	600						V
Maximum RMS Voltage	VRMS	424						V
Maximum DC Blocking Voltage	VDC	600						V
Maximum Average Forward Rectified Current	I (AV)	4	5	6	8	10	15	A
Peak Forward Surge Current 8.3ms single Half Sine-Wave	IFSM	95	100	120	170	200	300	A
I <sup>2</sup> t Rating for Fusing	I <sup>2</sup> t	37	41	59	119	166	373	A <sup>2</sup> s
Peak repetitive reverse current at tp = 2us , 1 kHz	IRRM	10						mA
Operating Temperature Range	TJ	-55 to +150						°C
Storage Temperature Range	TSTG	-55 to +175						°C
Breakdown Voltage per Diode	VBR	600						V
Forward Voltage IF@I(AV)/2 , TJ=25°C IF@I(AV)/2 , TJ=125°C IF@I(AV) , TJ=25°C IF@I(AV) , TJ=125°C	VF	0,99 0,86 1,09 0,97						V
Maximum DC Reverse Current @TJ= 25°C At Rated DC Blocking Voltage @TJ= 125°C	IR	3,2 0,32						uA mA
Maximum Reverse Recovery Time	Trr	500						ns
Typical Junction Capacitance	CJ	25	33	36	52	61	92	pF